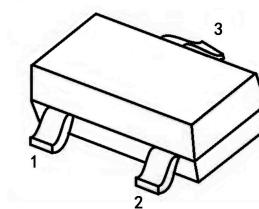


**KY1012****20V N-Channel Mosfet****FEATURES**

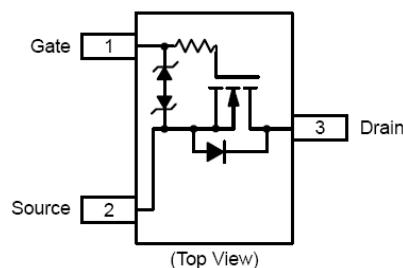
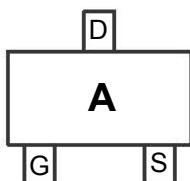
- $R_{DS(ON)} \leq 0.7\Omega$ (0.41Ω Typ.)
@ $V_{GS}=4.5V$
- $R_{DS(ON)} \leq 0.85\Omega$ (0.53Ω Typ.)
@ $V_{GS}=2.5V$
- $R_{DS(ON)} \leq 1.25\Omega$ (0.7Ω Typ.)
@ $V_{GS}=1.8V$

SOT-523

1. GATE
2. SOURCE
3. DRAIN

APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, displays, Memories
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, agers

N-CHANNEL MOSFET**MARKING****MAXIMUM RATINGS (Ta=25°C unless otherwise noted)**

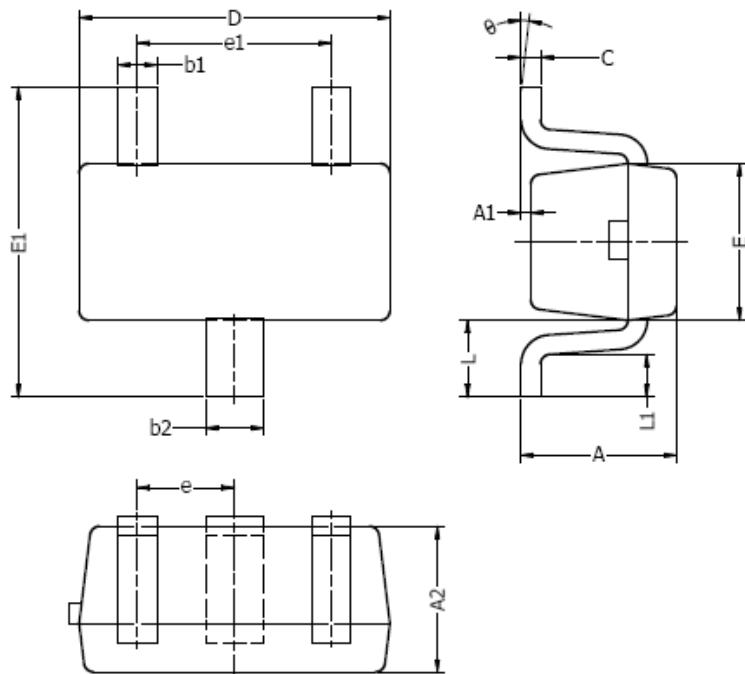
Symbol	Parameter		5 secs	Steady State	Units
V_{DS}	Drain-Source Voltage		20		V
V_{GS}	Gate-Source Voltage		$\pm 6V$		V
I_D	Continuous Drain Current	$T_a=25^\circ C$	600	500	mA
		$T_a=85^\circ C$	400	350	
I_{DM}	Pulsed Drain Current note1		1000		mA
I_S	Continuous Source Current		275	250	mA
P_D	Power Dissipation	$T_a=25^\circ C$	175	150	mW
		$T_a=85^\circ C$	90	80	
T_{STG}	Storage Temperature Range		-55 to +150		°C
T_J	Operating Junction Temperature		+150		°C
ESD	Gate-source ESD Rating (HBM, Method 3015)		2000		V



KY1012

MOSFET ELECTRICAL CHARACTERISTICS Ta=25 °C unless otherwise specified

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 20V, V _{GS} = 0V, T _J = 25°C	-	0.3	100	nA
I _{GSS}	Gate to Body Leakage Current	V _{GS} =±4.5V, V _{DS} =0V	-	±0.5	±1	μA
I _{D(ON)}	On-state Drain Current	V _{DS} =5V, V _{GS} =4.5V	700	-	-	mA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D = 100μA	0.45	-	0.9	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =4.5V, I _D =600mA	-	0.41	0.70	Ω
		V _{GS} =2.5V, I _D =500mA	-	0.53	0.85	
		V _{GS} =1.8V, I _D =350mA	-	0.70	1.25	
g _{FS}	Forward Transconductance	V _{DS} =10V, I _D =400mA	1	-	-	mS
Dynamic Characteristics						
Q _g	Total Gate Charge	V _{DS} =10V, I _D =250mA V _{GS} =4.5V	-	750	-	nC
Q _{gs}	Gate-Source Charge		-	75	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	225	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{GS} =4.5V, V _{DS} =10V, R _G =10Ω, I _D =200mA R _L =47Ω	-	5	-	ns
t _r	Turn-On Rise Time		-	5	-	ns
t _{d(off)}	Turn-Off Delay Time		-	25	-	ns
t _f	Turn-Off Fall Time		-	11	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, T _J = 25°C I _{SD} =150mA	-	0.8	1.2	V

KY1012**SOT-523 PACKAGE OUTLINE DRAWING**

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.70	0.90	0.028	0.035
A1	0.00	0.10	0.000	0.004
A2	0.70	0.80	0.028	0.031
b1	0.15	0.25	0.006	0.010
b2	0.25	0.35	0.010	0.014
c	0.10	0.20	0.004	0.008
D	1.50	1.70	0.059	0.067
E	0.70	0.90	0.028	0.035
E1	1.45	1.75	0.057	0.069
e	0.50 TYP.		0.020 TYP.	
e1	0.90	1.10	0.035	0.043
L	0.40 REF.		0.016 REF.	
L1	0.10	0.30	0.004	0.012
θ	0 °	8 °	0 °	8 °

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